

## P-Channel 1.25-W, 1.8-V (G-S) MOSFET

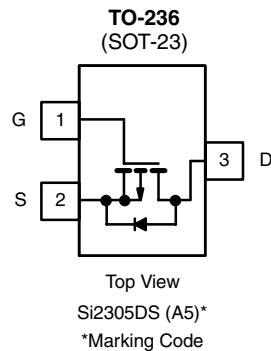
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 8	0.052 at $V_{GS} = - 4.5$ V	$\pm 3.5$
	0.071 at $V_{GS} = - 2.5$ V	$\pm 3$
	0.108 at $V_{GS} = - 1.8$ V	$\pm 2$

### FEATURES

- TrenchFET<sup>®</sup> Power MOSFETs: 1.8 V Rated



**RoHS\***  
COMPLIANT



**Ordering Information:** Si2305DS-T1  
Si2305DS-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 8	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_A = 25$ °C	$\pm 3.5$
		$T_A = 70$ °C	$\pm 2.8$
Pulsed Drain Current	$I_{DM}$	$\pm 12$	A
Continuous Source Current (Diode Conduction) <sup>a, b</sup>	$I_S$	- 1.6	
Maximum Power Dissipation <sup>a, b</sup>	$P_D$	$T_A = 25$ °C	1.25
		$T_A = 70$ °C	0.8
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 5$ sec	100	°C/W	
		Steady State	130		

Notes:

a. Surface Mounted on FR4 Board.

b.  $t \leq 5$  sec.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

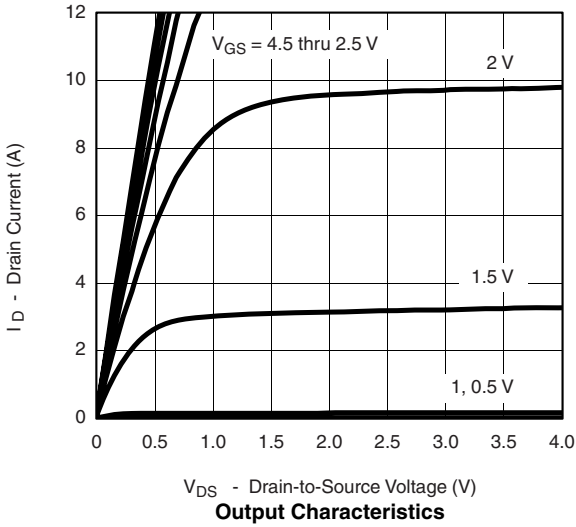
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$	- 8			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.45		- 0.8	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 6			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -2.5\text{ V}$	- 3			
Drain-Source On-Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -3.5\text{ A}$		0.044	0.052	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -3\text{ A}$		0.060	0.071	
		$V_{GS} = -1.8\text{ V}, I_D = -2\text{ A}$		0.087	0.108	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -3.5\text{ A}$		8.5		S
Diode Forward Voltage	$V_{SD}$	$I_S = -1.6\text{ A}, V_{GS} = 0\text{ V}$			- 1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D \cong -3.5\text{ A}$		10	15	nC
Gate-Source Charge	$Q_{gs}$			2		
Gate-Drain Charge	$Q_{gd}$			2		
Input Capacitance	$C_{iss}$	$V_{DS} = -4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1245		pF
Output Capacitance	$C_{oss}$			375		
Reverse Transfer Capacitance	$C_{rss}$			210		
<b>Switching<sup>b</sup></b>						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		13	20	ns
	$t_r$			25	40	
Turn-Off Time	$t_{d(off)}$			55	80	
	$t_f$			19	35	

## Notes:

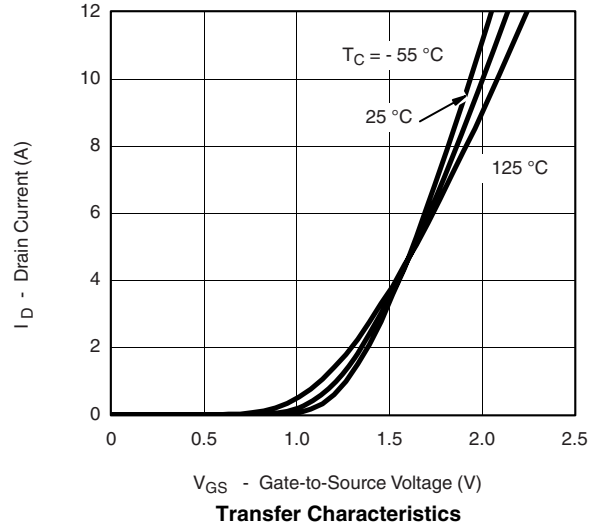
- a. For DESIGN AID ONLY, not subject to production testing.  
 b. Pulse test:  $PW \leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

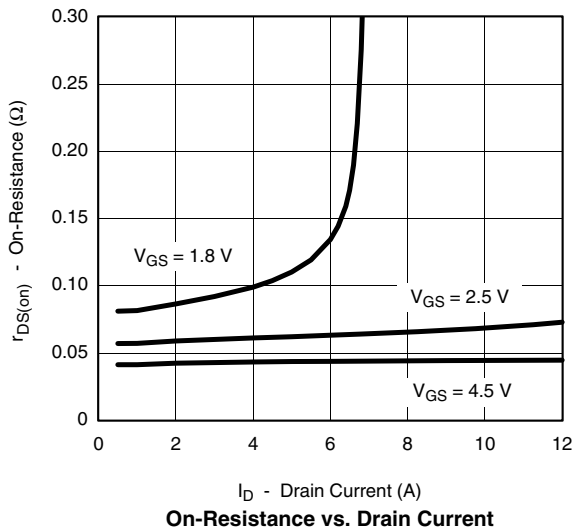
## TYPICAL CHARACTERISTICS 25 °C, unless noted



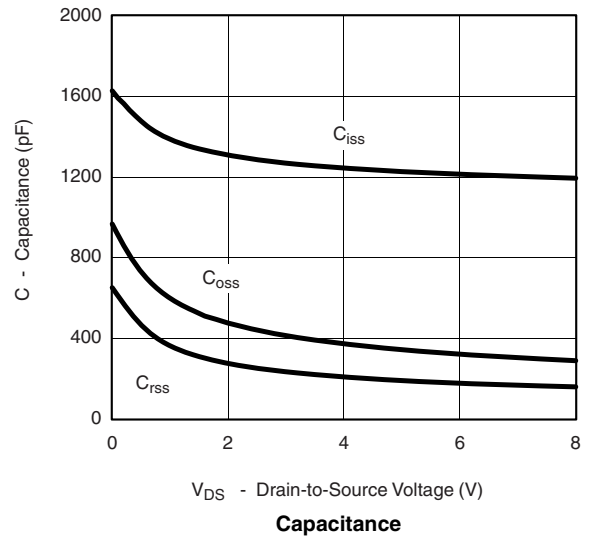
Output Characteristics



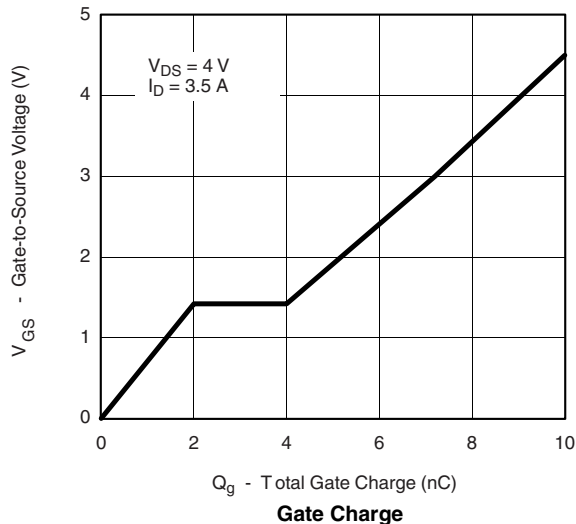
Transfer Characteristics



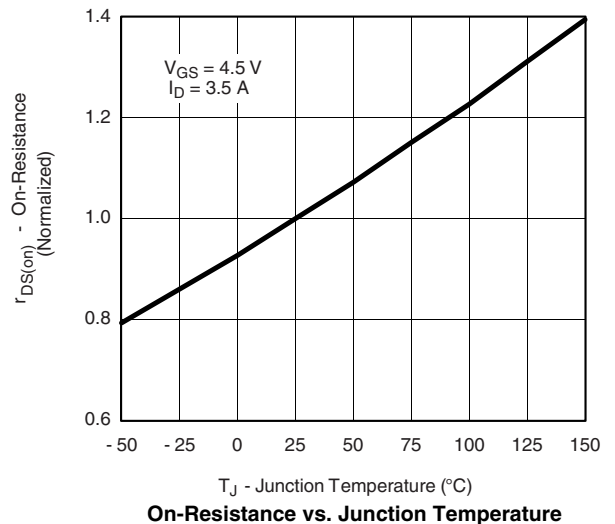
On-Resistance vs. Drain Current



Capacitance

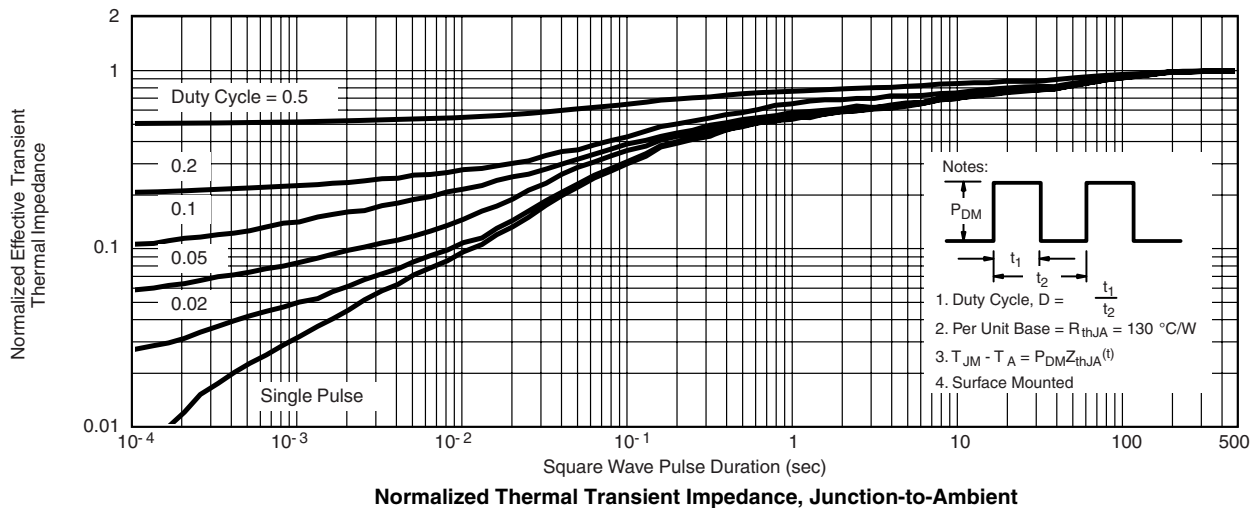
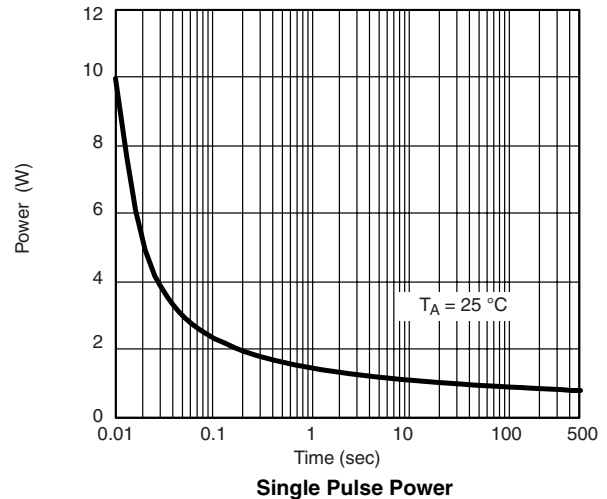
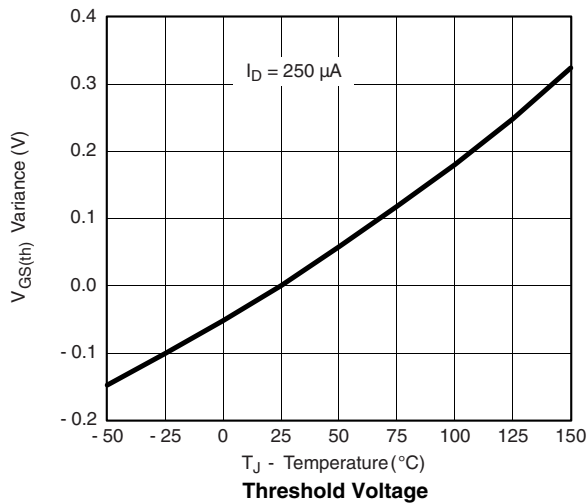
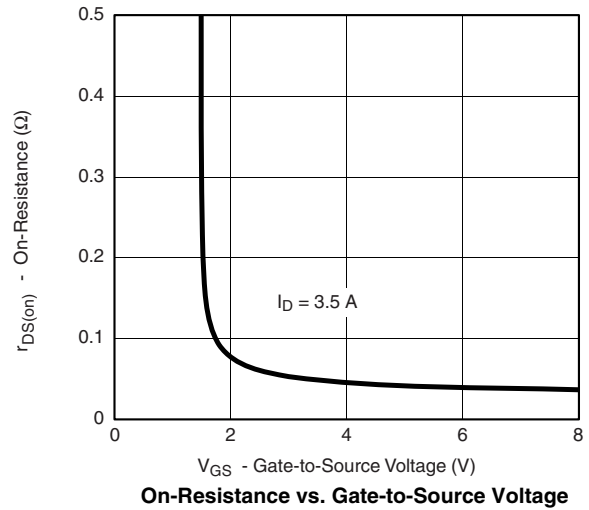
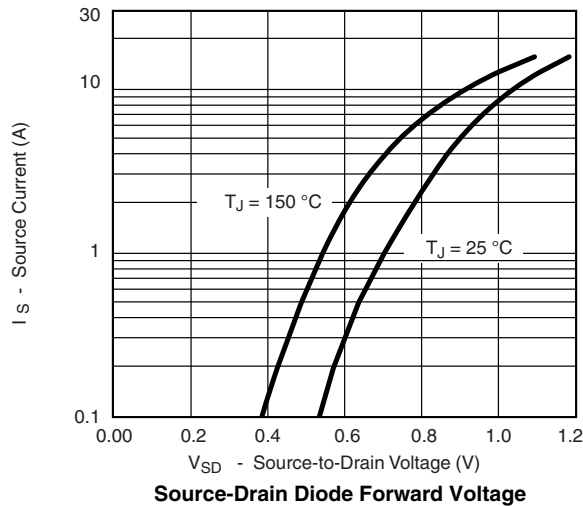


Gate Charge



On-Resistance vs. Junction Temperature

**TYPICAL CHARACTERISTICS** 25 °C, unless noted



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